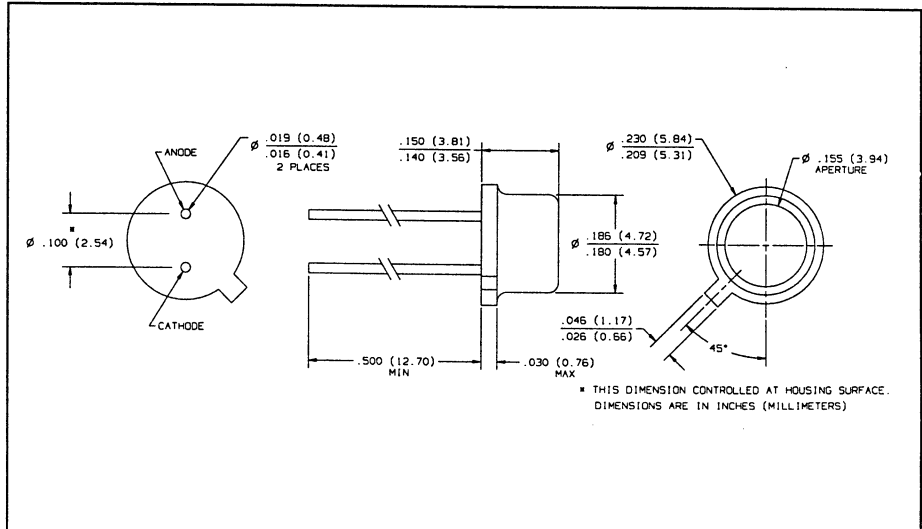
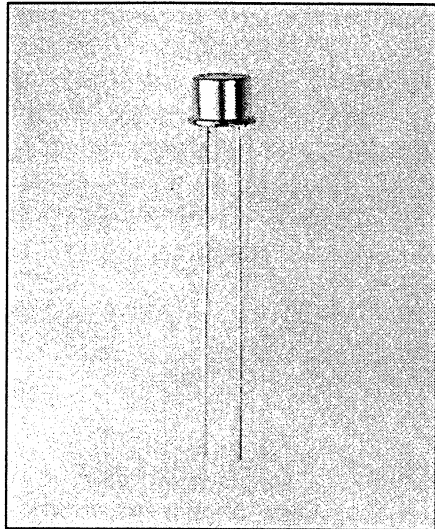


GaAs Hermetic Infrared Emitting Diodes Types OP130W, OP131W, OP132W, OP133W



Features

- Wide irradiance pattern
- Enhanced temperature range
- Mechanically and spectrally matched to the OP800WSL and OP830WSL series devices
- Variety of power ranges
- TO-46 hermetically sealed package

Description

The OP130W series devices are 935nm gallium arsenide infrared emitting diodes mounted in hermetically sealed packages. The broad irradiance pattern provides relatively even illumination over a large area.

Replaces

K6200 series

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Reverse Voltage	2.0 V
Continuous Forward Current	100 mA
Peak Forward Current (2 μs pulse width, 0.1% duty cycle)	10.0 A
Storage Temperature Range	-65°C to $+150^\circ\text{C}$
Operating Temperature Range	-65°C to $+125^\circ\text{C}$
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 sec. with soldering iron]	$260^\circ\text{C}^{(1)}$
Power Dissipation	$200\text{ mW}^{(2)}$

Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 seconds max. when flow soldering.
- (2) Derate linearly $2.0\text{ mW}/^\circ\text{C}$ above 25°C .
- (3) Measurement made with 100 μs pulse measured at the trailing edge of the pulse with a duty cycle of 0.1% and an $I_F = 100\text{ mA}$.

Typical Performance Curves

Coupling Characteristics
of OP130W and OP800W

